

SN. 10/617,487

ATTORNEY DOCKET NO. SALA:003

IN THE CLAIMS

The status of the claims as presently amended is as follows:

1. (Currently Amended) A lateral double-diffused MOSFET semiconductor device comprising:
 - a substrate;
 - an epitaxial layer formed on the substrate;
 - a well region formed in the epitaxial layer;
 - a source region formed in the well region;
 - a drain region formed in the epitaxial region;
 - a gate region located above at least a portion of the well region; and
 - a ~~split-drift~~ drift region in the epitaxial layer and comprised of a super-junction region and a RESURF region, located between the source region and the drain region,wherein the RESURF region is positioned between the super-junction region and the drain region.
2. (Cancel)
3. (Currently Amended) The device of Claim [[2]]1, wherein the super-junction ~~portion~~ region is positioned adjacent to ~~between~~ the well region and the RESURF region.
4. (Currently Amended) The device of Claim [[2]]1, wherein the super-junction ~~portion~~ comprises alternatively arranged pillars of first and second conductivity types ~~region~~ comprises a plurality of alternatively arranged first semiconductor region of a first conductivity type and second semiconductor region of a second conductivity type.
5. (Currently Amended) The device of Claim [[2]]1, wherein the ~~reduced surface field~~ ~~portion~~ RESURF region is located adjacent to the drain region.
6. (Currently Amended) The device of Claim 5, wherein the ~~reduced surface portion~~ RESURF region comprises a first conductivity type and the substrate comprises a second conductivity type.
7. (Currently Amended) The device of Claim [[2]]1, wherein the length of the ~~reduced surface field portion~~ RESURF region is ~~much~~ substantially less than the length of the super-junction ~~portion~~ region.

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8. *(Currently Amended)* The device of Claim 7, wherein the product of the doping concentration and the vertical thickness of the reduced surface field portion and the vertical thickness of the reduced surface field portion RESURF region is about $2 \times 10^{12} \text{ cm}^{-2}$.

9. *(Currently Amended)* The device of Claim 4, wherein the product of the doping concentration and a width of each first or second semiconductor region of the super-junction pillars and a transverse pillar width region is about $2 \times 10^{12} \text{ cm}^{-2}$.

10. *(New)* The device of Claim 1, wherein the RESURF region is doped less than the super-junction region.

11. *(New)* The device of Claim 1, wherein the RESURF region is doped less than the drain region.

12. *(New)* The device of Claim 1, wherein the RESURF region is doped less than the super-junction region and the drain region.